

Figure 1
Prior Art

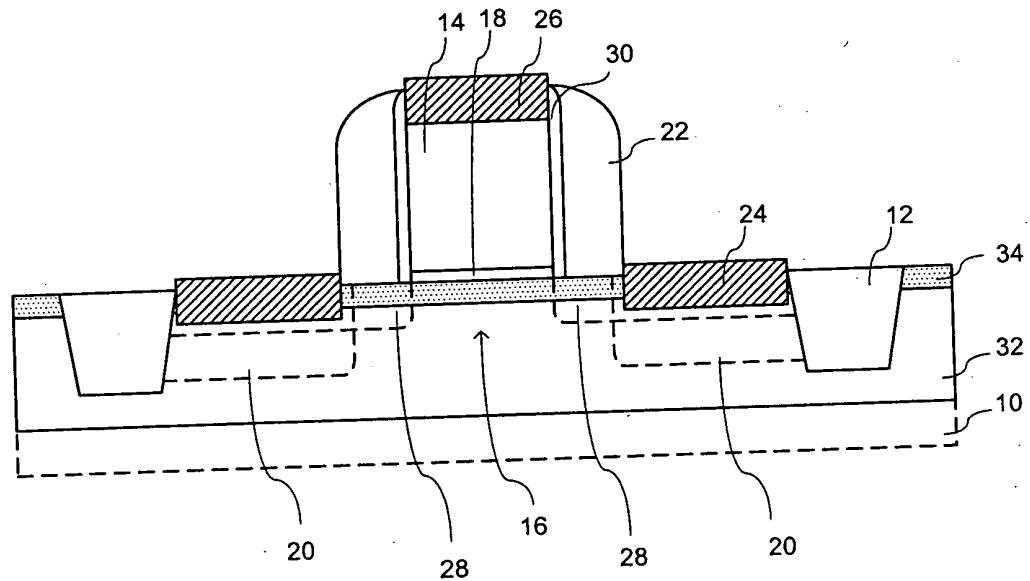


Figure 2
Prior Art

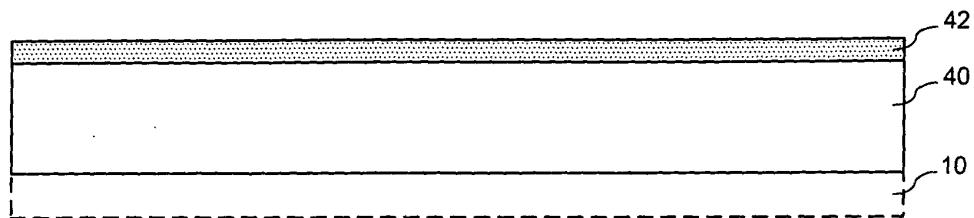


Figure 3a

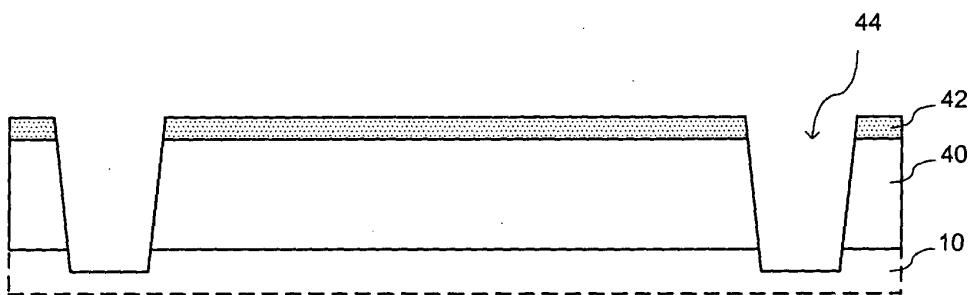


Figure 3b

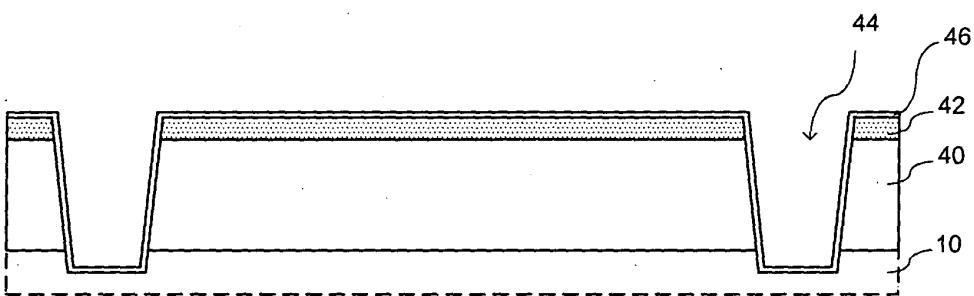


Figure 3c

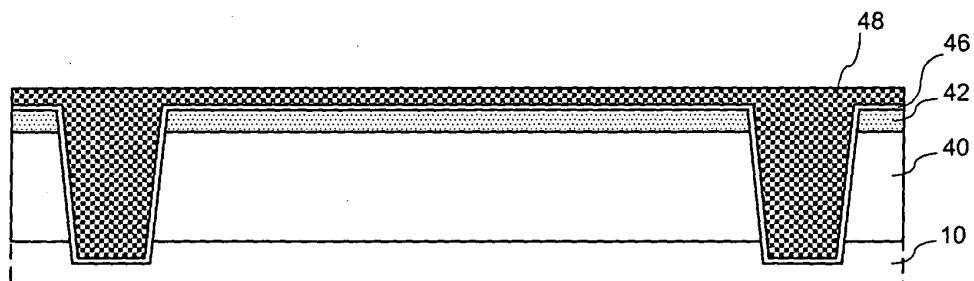


Figure 3d

STRAINED SILICON MOSFET HAVING
IMPROVED THERMAL CONDUCTIVITY AND
METHOD FOR ITS FABRICATION
Inventors: Jung-Suk Goo et al.
Attorney: Ronald Coslick - 039153-0676
FOLEY & LARDNER - (310) 277-2223
Sheet 3 of 7

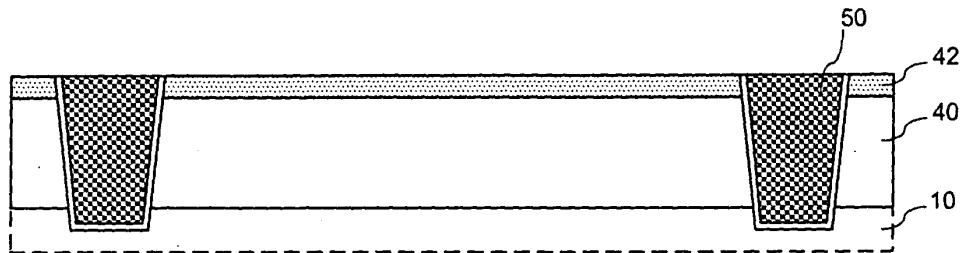


Figure 3e

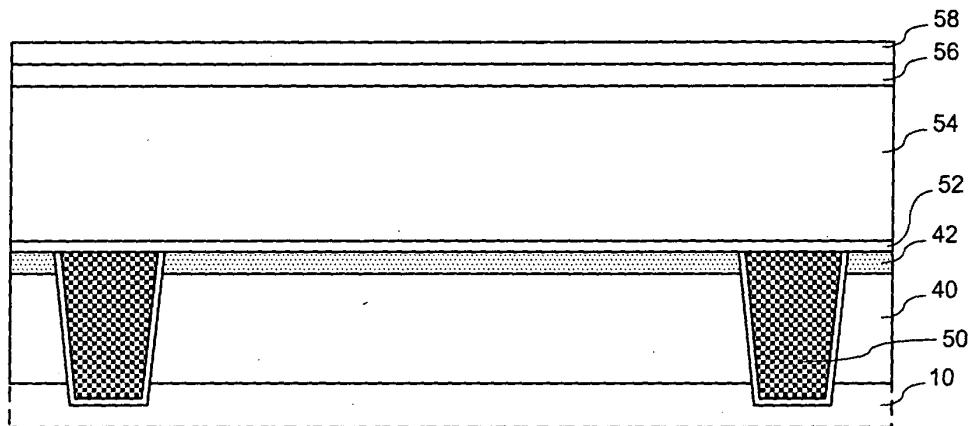


Figure 3f

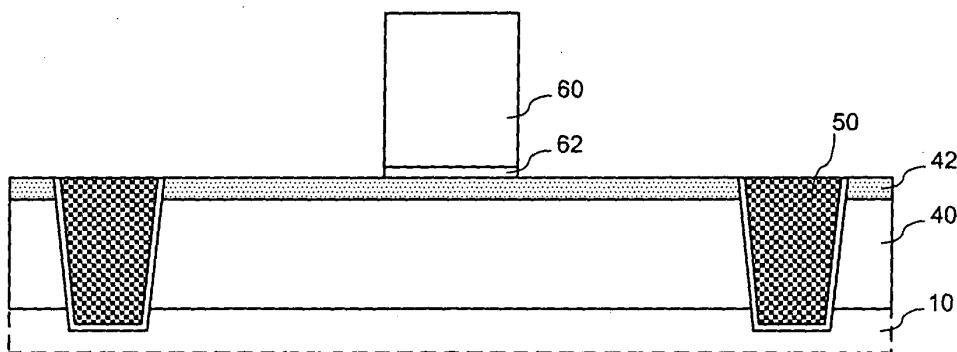


Figure 3g

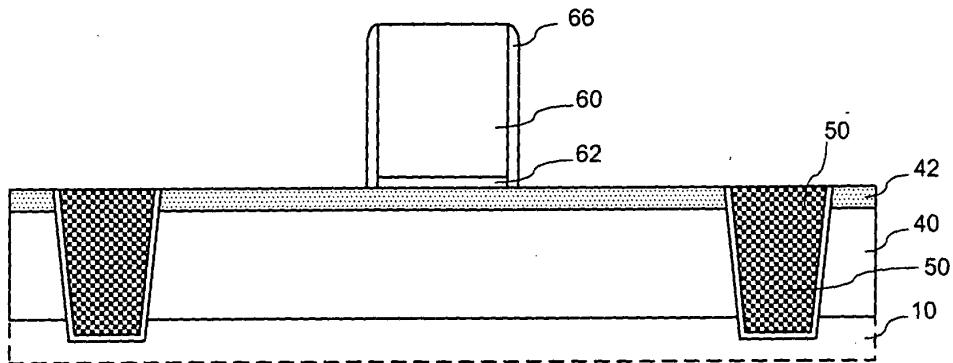


Figure 3h

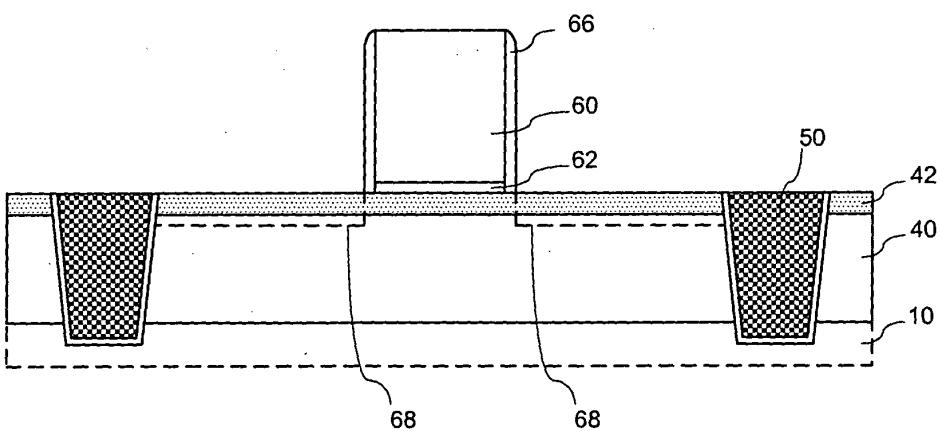


Figure 3i

STRAINED SILICON MOSFET HAVING
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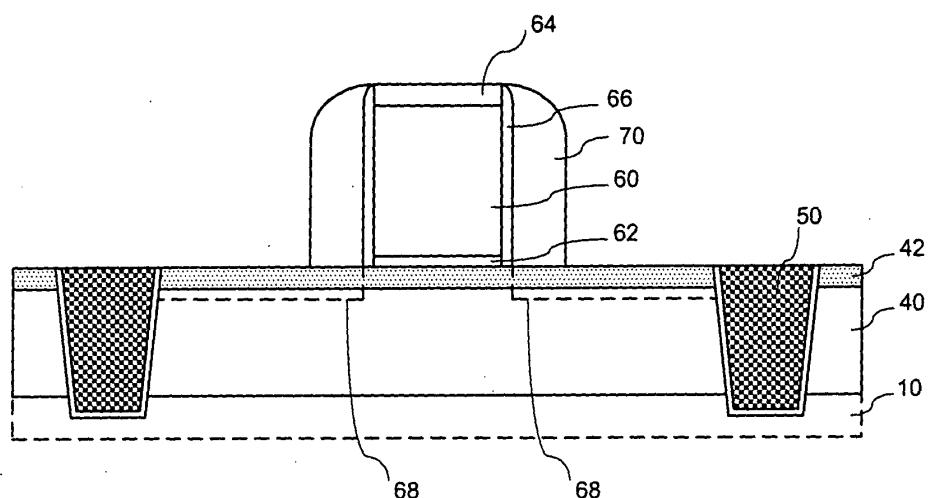


Figure 3j

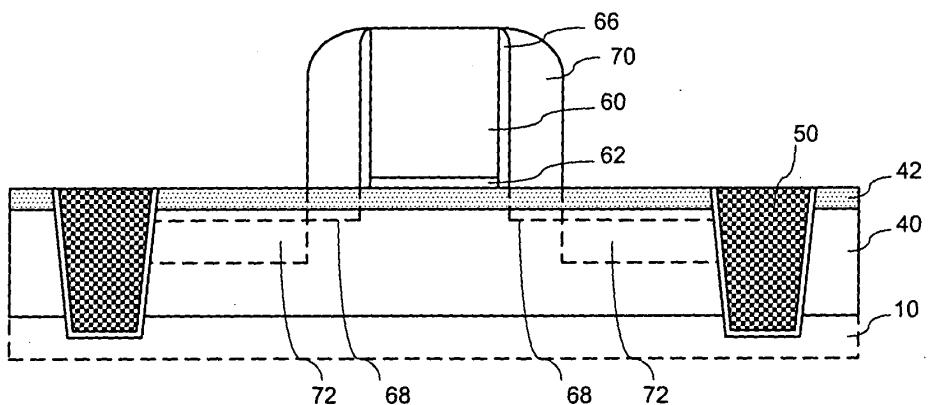


Figure 3k

STRAINED SILICON MOSFET HAVING
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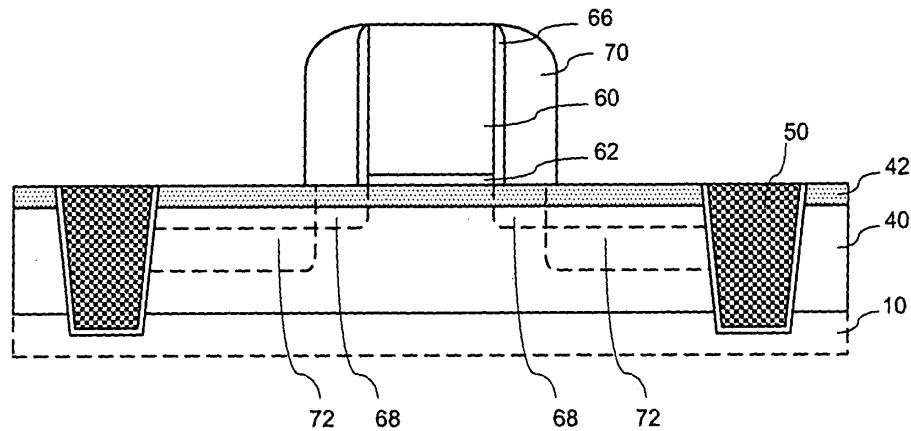


Figure 3L

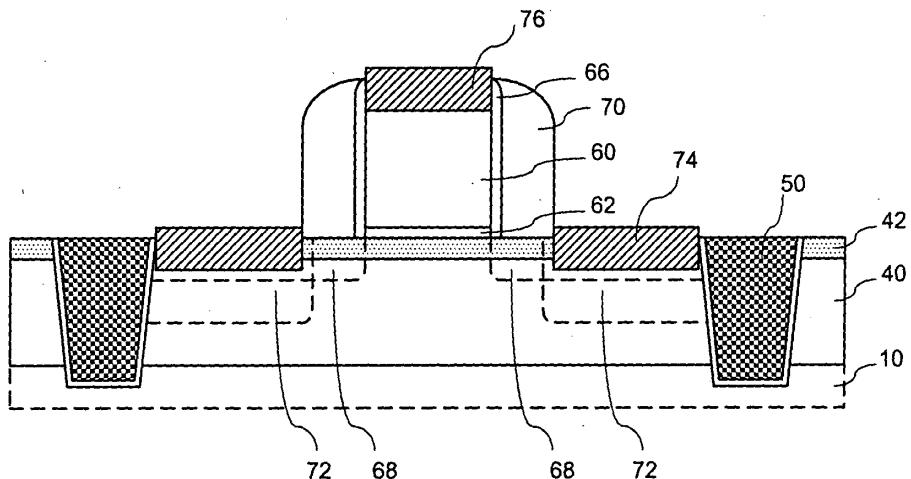


Figure 3m

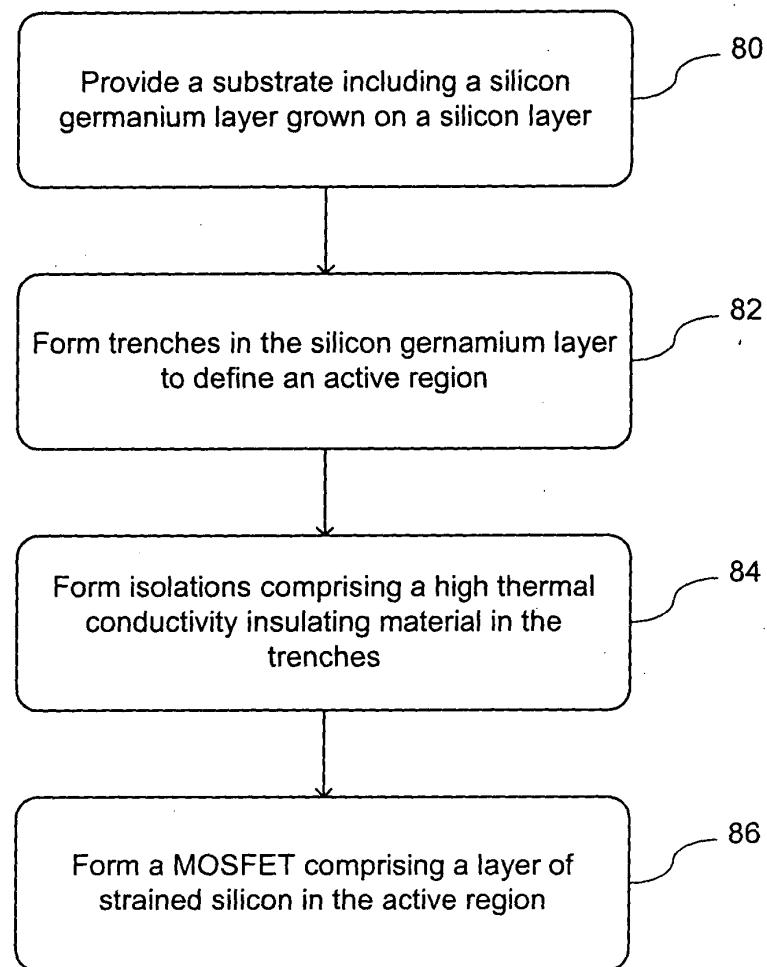


Figure 4